Thin films of crystallized LaCoO$_3$ were grown on Si substrate by Pulsed Laser Deposition at different temperatures (750°C, 850°C and 1000°C). The structural characterization of the LaCoO$_3$ thin films was done by combining several techniques: Scanning Electron Microscopy (SEM), Atomic Force Microscope (AFM), Transmission Electron Microscopy (TEM) and Grazing Incidence X-Ray Diffraction (GIXRD). The thin films crystallized in the expected rhombohedral phase whatever the deposition temperature, with an increase of crystallite size from 70 nm at 750°C to 100 nm at 1000°C, and an average thickness of the thin films of less than 200 nm. At 850°C and 1000°C, the thin films are crack-free, and with a lower number of droplets than the film deposited at 750°C. The grains of LaCoO$_3$ film deposited at 850°C are columnar, with a triangular termination. At 1000°C, an intermediate layer of La$_2$Si$_2$O$_7$ was observed, indicating diffusion of Si into the deposited film.

Keywords: PLD, thin films, perovskites, LaCoO$_3$

1. Introduction

Perovskites ABO$_3$ have attracted the interest of researchers because it is a promising class of materials especially in the electronic industry, due to their electrical conductivity properties [1-4]. But these materials are also popular as sensing medium in gas detection devices because of their high thermal stability and good catalytic properties [5-8]. LaCoO$_3$ has been established as a promising material for resistive sensors [9], electrochemical sensors [10], temperature sensors [11], as well as catalysts and photocatalysts [12]. These perovskites have very good catalytic properties in the presence of gases such as CO, NO$_x$, and H$_2$S [13-15].

LaCoO$_3$ based sensors in the form of thin films were recently tested for CO detection [16]. The films showed a high response, excellent recovery and good stability to CO gas at low-temperature $T = 200°C$. LaCoO$_3$ nanoparticles with the perovskite-type structure were successfully synthesized by Ortiz et al. [17]. The LaCoO$_3$ pellets presented a high sensitivity for both CO and CH$_4$ at different concentrations and operating temperatures.

Various preparation methods are reported for the synthesis of LaCoO$_3$ thin films or powders like sol-gel, CVD, PVD or PLD [18-21]. All these methods and their parameters influence the structural morphology, phase or chemical composition and hence the properties of the material. In case of thin films for gas sensors, the morphology of the surface of the thin films, the grain size and crystallographic orientation, as well as the exposed facets influenced the response time and sensitivity to the gas of interest. Grains in the nanometer range result in a higher reactive surface and higher sensitivity of the gas sensor. The surface state is also important as was stated by Say et al [14] in their comparative study of the perfect and the oxygen defective LaCoO$_3$ (001) surfaces.

The aim of this primary work on the synthesis of LaCoO$_3$ thin films by Pulsed Laser Deposition (PLD) was to investigate the influence of process temperature on the morphology and crystallographic structure of the obtained thin films deposited on silicon (Si) substrates in presence of oxygen.

2. Methodology

The LaCoO$_3$ (99,9%) target (diameter = 2,5 cm) was purchased from the Kurt J. Lesker Company. The thin films were deposited on (100) oriented Si substrates purchased from the
SurfaceNet GmbH (10×10 mm, Ra < 0.5 nm) using a laser ablation system equipped with a Nd-YAG (λ = 266 nm) laser and a Neocera chamber, in presence of oxygen (40 mTorr), at 3 different substrate temperatures 750°C, 850°C and 1000°C. The deposition conditions were a laser pulse frequency of 10 Hz, and energy density on the target of 7.8 J/cm², a laser pulse duration of 4 ns and a deposition time fixed at 2.5 hours. The phase analyses of the thin films were performed by means of the X-ray diffraction method using PAN analytical EMPYREAN DY 1061 equipped with a Cu Kα tube, in Bragg-Brentano geometry and grazing angles of 1° and 3°. The X rays diffraction patterns were refined using the software MAUD and cif files. The morphology of the thin films were studied by SEM using a Zeiss Supra 40, and by TEM, using a Tecnai G2 operating at 200 kV, on cross-sectional samples, prepared in a conventional way, through mechanical thinning followed by low angles ion milling. The film roughness was analyzed by AFM using a Veeco Dimension® Icon™ SPM with the NanoScope V instrument.

3. Results and discussion

The XRD pattern are presented Fig. 1. The corresponding depth of penetration is \( z = 54 \) nm. The identification of phases was assessed thanks to the JCPDS database, specifically the card numbers 04-009-4883. The three diffractions patterns correspond to the expected rhombohedral phase for LaCoO\(_3\). The peak intensity changes with the temperature of the substrate, with (012) being the most intense peak for \( T = 750°C \) to (110) being the most intense one for \( T = 850°C \) and \( T = 1000°C \), in the \( 2θ \) range 20–40°. However, determining the preferred orientation (texture analysis) is not straightforward due to the changes in the reflection vector \( q \) in grazing geometry compared to Bragg Brentano geometry [22].

Cell parameters, angle \( α \) (°), cell volume, and reliability factors (weighted profile \( R - factor \) – \( R_{wp} \), expected \( R \) factor – \( R_{exp} \)), deduced from the X rays diffraction patterns refinements, are given in Table 1.

<table>
<thead>
<tr>
<th>Sample</th>
<th>( a (Å) )</th>
<th>( α (°) )</th>
<th>( V (Å^3) )</th>
<th>( R_{exp}/R_{wp} )</th>
</tr>
</thead>
<tbody>
<tr>
<td>LaCoO(_3)-750</td>
<td>5.4199</td>
<td>60.72</td>
<td>114.41</td>
<td>4.32/6.79</td>
</tr>
<tr>
<td>LaCoO(_3)-850</td>
<td>5.3971</td>
<td>60.69</td>
<td>112.90</td>
<td>6.90/10.56</td>
</tr>
<tr>
<td>LaCoO(_3)-1000</td>
<td>5.3979</td>
<td>60.67</td>
<td>112.90</td>
<td>6.25/9.16</td>
</tr>
</tbody>
</table>

Table 1

The cell parameter as well the \( α \) angle slightly decreases with increasing deposition temperature. This can be linked to the presence of cobalt vacancies in the layers [23].

The surface morphology of thin films is of great importance in the case of gas sensing applications because the crystallographic facets exposed to the gas may govern the detection properties. Fig. 2 shows SEM images of the surface morphology for the different layers. The LaCoO\(_3\)-750 layer is characterized by the presence of cracks and a big number of droplets (Fig. 2a). The mean grain size is around 70 nm. The LaCoO\(_3\)-850 layer (Fig. 2b) shows an interesting specific morphology, with triangular grains and a flat termination and a small number of droplets. This grain shape is consistent with a [111] growth direction, which corresponds to the [111] direction of the pseudo-cubic perovskite cell. The grain size for the LaCoO\(_3\)-850 layer is around 100 nm. Moreover, no cracks were observed in this layer. This triangular shape is lost for the LaCoO\(_3\)-1000 thin film (Fig. 2c), where grains still have flat termination but with irregular shapes, some of them being characteristic of a [001] growth direction.

The topography of the surface was analyzed by AFM, carried out different area sizes, from 1 mm × 1 mm, to 100 nm × 100 nm. Selected results are presented on Fig. 3. The influence of deposition temperature is visible on the surface topography. For LaCoO\(_3\)-750, the surface is covered by small droplets (Fig. 3a). Similarly, the surface LaCoO\(_3\)-850 (Fig. 3b) contains droplets but larger and much less frequent. LaCoO\(_3\)-1000 is free from droplets (Fig. 3c).

The roughness parameters \( R_{max} \), \( R_s \), and \( R_q \), determined on regions free of droplets, are presented in Table 2.
TABLE 2

<table>
<thead>
<tr>
<th>Sample</th>
<th>$R_a$ [nm]</th>
<th>$R_{max}$ [nm]</th>
<th>$R_q$ [nm]</th>
</tr>
</thead>
<tbody>
<tr>
<td>LaCoO$_3$-750</td>
<td>1.27</td>
<td>16.5</td>
<td>1.67</td>
</tr>
<tr>
<td>LaCoO$_3$-850</td>
<td>1.54</td>
<td>11.9</td>
<td>1.92</td>
</tr>
<tr>
<td>LaCoO$_3$-1000</td>
<td>2.51</td>
<td>20.0</td>
<td>3.13</td>
</tr>
</tbody>
</table>

Thin films obtained at high temperatures are characterized by higher roughness parameters. The increase of $R_a$ parameters is a consequence of the change in morphology and an increase of grain size.

In order to obtain information about the thickness of thin films and the grain growth, as well as chemical composition, TEM analysis coupled with EDS were performed on cross-sectional samples. EDS analysis showed that the films have a homogeneous composition. The quantification, using the La-CoO$_3$ target as standard, evidenced a deficiency in cobalt (see Table 3). This result is in accordance with the XDR results. EDS also confirms that the droplets and layers composition have the same chemical composition. This slight cobalt deficiency could be due to the low oxygen pressure (40 mTorr) in the deposition chamber [24].

TABLE 3

<table>
<thead>
<tr>
<th>Element</th>
<th>Atomic %</th>
</tr>
</thead>
<tbody>
<tr>
<td>La (L)</td>
<td>56</td>
</tr>
<tr>
<td>Co (K)</td>
<td>44</td>
</tr>
</tbody>
</table>

TEM results are summarized in Fig. 4. In all images, a native SiO$_2$ layer is visible between the LaCoO$_3$ film and the Si
substrate. For LaCoO$_3$-750 and -850, the grain growth is columnar, with an average layer thickness of 170 nm (Fig. 4a & b). In Fig. 4a droplets are observed on top of the layer.

The roughness of the LaCoO$_3$-750 thin film seems rather low on TEM images, and a higher roughness is observed for LaCoO$_3$-850 (Fig. 4b), which is consistent with the AFM results.

Columns with regular triangular tips (75-100 nm) or a small flat termination can be observed; the lateral grain size varies from 75 nm to 100 nm. On the contrary, LaCoO$_3$-1000 exhibits a completely different morphology when observed in cross-section (Fig. 4c). The layer consists indeed of two distinct phases, one identified as La$_2$SiO$_7$ by high-resolution electron microscopy with distance $d_{hkl}$ = 10.5 Å (see FFT in Fig. 4c), near the substrate, and a layer of LaCoO$_3$ grains on top. The presence of a La$_2$SiO$_7$ layer, 75-85 nm thick, indicates that at 1000°C, Si can diffuse through the native SiO$_2$ barrier and built a lanthanum silicate. Silicates were already observed in thin films obtained by PLD with a deposition temperature of 1100°C [25]. As XRD patterns were collected under grazing incidence, the depth penetration of X rays was insufficient to reach the La$_2$SiO$_7$ layer, which explains why no information about it was obtained by GIXRD. The LaCoO$_3$ grains grown on La$_2$SiO$_7$ have a different morphology than those grown on Si. This change in morphology is expected to have a strong effect on the sensing characteristic of the material.

4. Conclusion

The main objective of this research was to analyze the influence of substrate temperature during Pulsed Laser Deposition, on the structure and morphology of LaCoO$_3$ films, for gas sensor applications. The rise of deposition temperature leads to an increase in grain size and an elimination of droplets and cracks. Increase of the grain size (observed by SEM and TEM) and increase of the roughness parameter $R_a$ determined by AFM might have a positive impact on the sensitivity to gases due to the increase of the surface exposed to the gas. A low temperature (750°C) leads to the presence of cracks and droplets. A high temperature deposition (1000°C) is causing creation of additional phase of La$_2$SiO$_7$ and a modification of the grain morphology. A temperature of 850°C seems to be the most suitable elaboration temperature for gas sensing applications. Indeed, it leads to the growth of nanosized columnar grains with a triangular shape, implying that specific crystallographic facets will be exposed to the gases. As expected, a proper selection of the temperature is necessary for the control of the morphology of LaCoO$_3$ thin layers obtained by PLD.

Further studies will be carried out to evaluate the gas sensing characteristics of these layers, starting with resistivity measurements under gas. These data will be produced in a future report.

Fig. 4. TEM images of LaCoO$_3$ a) LaCoO$_3$-750, b) LaCoO$_3$-850, c) LaCoO$_3$-1000
Acknowledgements

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REFERENCES